**Amendments to the Claims**

Claims 1-7 (Previously Canceled).

8. (Previously Amended): The method of claim 16 wherein the etching comprises plasma etching.

9. (Previously Amended): The method of claim 16 wherein the etching comprises magnetically enhanced plasma etching.

10. (Previously Amended): The method of claim 16 wherein the etching comprises substantially anisotropic etching of the silicon nitride comprising layer.

Claims 11-13 (Previously Canceled).

14. (Previously Amended): The method of claim 16 wherein the etching chemistry comprises at least two fluorocarbons.

15. (Previously Amended): The method of claim 16 wherein the etching chemistry comprises at least three fluorocarbons.

16. (Currently Amended): A method of forming integrated circuitry comprising:

forming a layer comprising silicon nitride over a semiconductor substrate;

forming a patterned photoresist comprising masking layer over the silicon nitride layer, the patterned masking layer comprising mask openings therethrough; and

etching the silicon nitride comprising layer through the mask openings substantially selectively to the photoresist comprising layer using an etching chemistry ~~consisting essentially of~~ having reactive components consisting of ammonia and at least one fluorocarbon under etching conditions effective to substantially anisotropically etch the silicon nitride comprising layer, the etching chemistry comprising a volumetric ratio of all fluorocarbon to the ammonia of from 40:1 to 20:1 and providing increased selectivity to the photoresist comprising masking layer than would otherwise occur using identical etching chemistry and identical etching conditions without any ammonia.

Claims 17 and 18 (Previously Canceled).

19. (Original): The method of claim 16 wherein the fluorocarbon comprises a hydrofluorocarbon.

20. (Currently Amended): A method of forming integrated circuitry comprising:

forming a layer comprising silicon nitride over a semiconductor substrate;

forming a patterned photoresist comprising masking layer over the silicon nitride layer, the patterned masking layer comprising mask openings therethrough; and

etching the silicon nitride comprising layer through the mask openings substantially selectively to the photoresist comprising layer using an etching chemistry ~~consisting essentially of~~ having reactive components consisting of ammonia and at least one fluorocarbon under etching conditions effective to substantially anisotropically etch the silicon nitride comprising layer, the etching chemistry comprising a volumetric ratio of all fluorocarbon to the ammonia of from 40:1 to 20:1 and providing increased selectivity to the photoresist comprising masking layer than would otherwise occur using identical etching chemistry and identical etching conditions without any ammonia, wherein the fluorocarbon is at least one member selected from the group consisting of $C_4F_6$ and $C_5F_8$.

21. (Original): The method of claim 16 wherein the silicon nitride comprising layer consists essentially of silicon nitride.

Claims 22-46 (Previously Canceled).

47. (Previously Added): The method of claim 16 wherein the photoresist comprises 193 nanometer photoresist.

48. (Previously Added): The method of claim 16 comprising introducing the ammonia and fluorocarbon successively into a reaction chamber in which the substrate is received during the etching.

49. (Previously Added): The method of claim 16 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

50. (Previously Added): The method of claim 16 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the silicon nitride comprising layer being formed over a bulk semiconductor substrate, and the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

51. (Previously Added): The method of claim 20 wherein the fluorocarbon comprises $C_4F_6$.

52. (Previously Added): The method of claim 20 wherein the fluorocarbon comprises $C_5F_8$.

53. (Canceled).

54. (Previously Added): The method of claim 20 wherein the photoresist comprises 193 nanometer photoresist.

55. (Previously Added): The method of claim 20 comprising introducing the ammonia and fluorocarbon successively into a reaction chamber in which the substrate is received during the etching.

56. (Previously Canceled).

57. (Previously Added): The method of claim 20 wherein the etching comprises plasma etching.

58. (Previously Added): The method of claim 20 wherein the etching comprises magnetically enhanced plasma etching.

59. (Previously Added): The method of claim 20 wherein the etching comprises substantially anisotropic etching of the silicon nitride comprising layer.

60. (Previously Added): The method of claim 20 wherein the etching chemistry comprises at least two fluorocarbons.

61. (Previously Added): The method of claim 20 wherein the etching chemistry comprises at least three fluorocarbons.

62. (Previously Canceled).

63. (Previously Added): The method of claim 20 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

64. (Previously Added): The method of claim 20 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the silicon nitride comprising layer being formed over a bulk semiconductor substrate, and the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.